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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/698,167	10/30/2003	Mohammad R. Mirabedini	02-6352/LSIIP220 9841	
24319 7	590 01/06/2005		EXAMINER	
LSI LOGIC CORPORATION			PRENTY, MARK V	
1621 BARBER LANE				
MS: D-106			ART UNIT	PAPER NUMBER
MILPITAS, C	A 95035		2822	

DATE MAILED: 01/06/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

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••		Application No.	Applicant(s)
		10/698,167	MIRABEDINI ET AL.
	Office Action Summary	Examiner	Art Unit
7.00		MARK V PRENTY	2822
Period fo	The MAILING DATE of this communication app or Reply	pears on the cover sheet with the c	correspondence address
THE - Exte after - If the - If NC - Failt Any	MORTENED STATUTORY PERIOD FOR REPL' MAILING DATE OF THIS COMMUNICATION. ensions of time may be available under the provisions of 37 CFR 1.1: r SIX (6) MONTHS from the mailing date of this communication. e period for reply specified above is less than thirty (30) days, a reply to period for reply is specified above, the maximum statutory period were to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing the patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be ting within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	mely filed ys will be considered timely. h the mailing date of this communication. ED (35 U.S.C. § 133).
Status			
1)⊠ 2a)□ 3)□	Responsive to communication(s) filed on 30 O This action is FINAL . 2b) This Since this application is in condition for allowar closed in accordance with the practice under E	action is non-final. nce except for formal matters, pr	
Disposit	ion of Claims		
5)⊠ 6)⊠	Claim(s) <u>1-26</u> is/are pending in the application. 4a) Of the above claim(s) is/are withdraw Claim(s) <u>1-6 and 8-26</u> is/are allowed. Claim(s) <u>7</u> is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction and/or	wn from consideration.	
Applicat	ion Papers		•
10)⊠	The specification is objected to by the Examine The drawing(s) filed on <u>30 October 2003</u> is/are: Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the Ex	: a)⊠ accepted or b)⊡ objected drawing(s) be held in abeyance. Se ion is required if the drawing(s) is ob	e 37 CFR 1.85(a). ojected to. See 37 CFR 1.121(d).
Priority (under 35 U.S.C. § 119		
a)	Acknowledgment is made of a claim for foreign All b) Some * c) None of: 1. Certified copies of the priority document: 2. Certified copies of the priority document: 3. Copies of the certified copies of the priority application from the International Bureau See the attached detailed Office action for a list	s have been received. s have been received in Applicat rity documents have been receiv u (PCT Rule 17.2(a)).	ion No ed in this National Stage
Attachmen	ut(s) ce of References Cited (PTO-892)	4) 🔲 Interview Summary	r (PTO-413)
2)	ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) er No(s)/Mail Date	Paper No(s)/Mail D	

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This Office Action is in response to the papers filed on October 30, 2003.

Claim 7 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Specifically, independent claim 1 recites, "a calcium and boron doped polysilicon gate electrode on the gate dielectric," but claim 7, which depends on claim 1, inconsistently recites "wherein the calcium is present in a thin atomic layer at the gate electrode/gate dielectric interface" (i.e., independent claim 1 recites that the polysilicon gate is doped with calcium, but dependent claim 7 inconsistently recites that claim 1's calcium is a thin atomic layer separate from the polysilicon gate – note the specification at paragraph [0033]).

Claims 1-6 and 8-26 are allowable over the prior art of record.

The prior art of record does not disclose or suggest to one skilled in the art the allowable semiconductor device and method of making a semiconductor device taken as a whole, including the calcium and boron doped polysilicon gate electrode.

United States Patent 4,755,865 (Wilson et al.), United States Patent 5,937,303 (Gardner et al.), United States Patent 6,373,113 (Gardner et al.), United States Patent Application Publication 2003/0168705 (Tanida et al.), United States Patent Application Publication 2004/0089887 (Aronowitz et al.), United States Patent Application Publication 2004/0110328 (Aronowitz et al.) and United States Patent Application Publication 2004/0121550 (Zubkov et al.) are relevant to this application.

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Registered practitioners can telephone the examiner at (571) 272-1843. Any voicemail message left for the examiner must include the name and registration number of the registered practitioner calling, and the Application/Control (Serial) Number. Technology Center 2800's general telephone number is (571) 272-2800.

Mark V. Prenty Primary Examiner